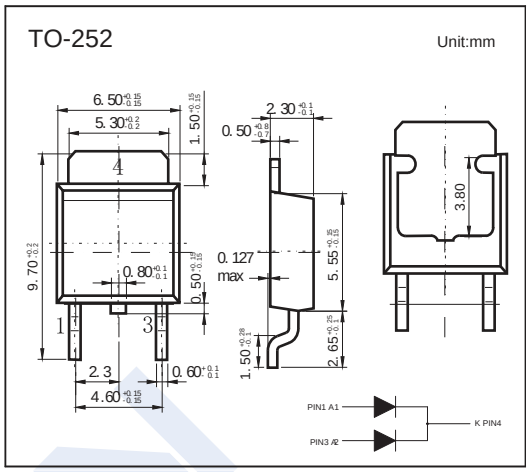
Schottky Diodes

MBR640CS~MBR6200CS



■ Features

- Low power loss, high efficiency.
- Low forwrd voltage, high current capability
- High surge capacity.
- For use in low voltage,high frequency inverters.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	MBR 640CS	MBR 645CS	MBR 650CS	MBR 660CS	MBR 680CS	MBR 690CS	MBR 6100CS	MBR 6150CS	MBR 6200CS	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40	45	50	60	80	90	100	150	200	V
Surge Peak Reverse Voltage	V_{RSM}	28	31.5	35	42	56	63	70	105	140	
Maximum DC Blocking Voltage	V_{DC}	40	45	50	60	80	90	100	150	200	
Forward Voltage @ I_F=3A	V_F	0.7		0.75		0.8			0.9		
Averaged Forward Current	I_{FAV}	6									A
Averaged Forward Current(Each Diode)		3									
Peak Forward Surge Current Ta=25℃	I_{FSM}	75									
Maximum DC Reverse Current Ta=25℃	I_R	0.05									mA
Ta=100℃		20									
Typical Thermal Resistance *1	R_{thJC}	3									℃/W
	R_{thJA}	60									
Junction Temperature	Tj	150									℃
Storage Temperature	Tstg	-55 to 150									

* 1 Device mounted on P.C.B., with minimum pad layout.

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■ Typical Characterisitics

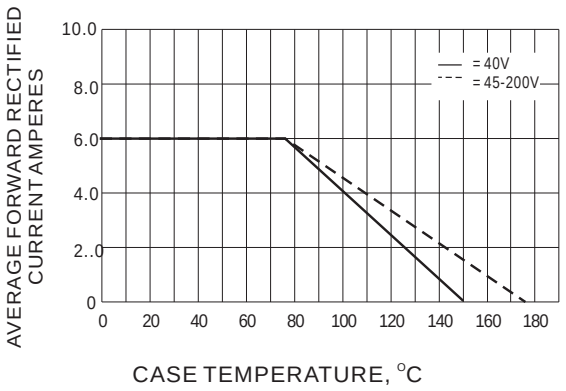

Fig.1- FORWARD CURRENT DERATING CURVE

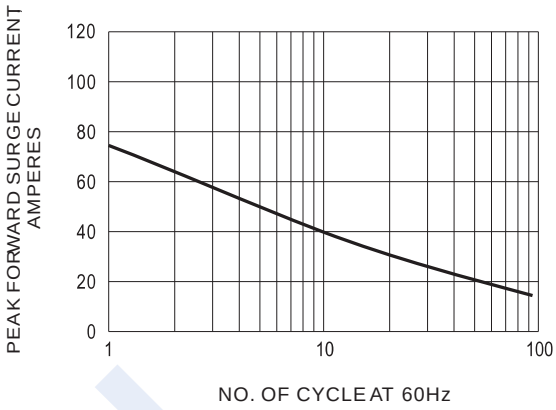

Fig.2- MAXIMUM NON - REPETITIVE SURGE CURRENT

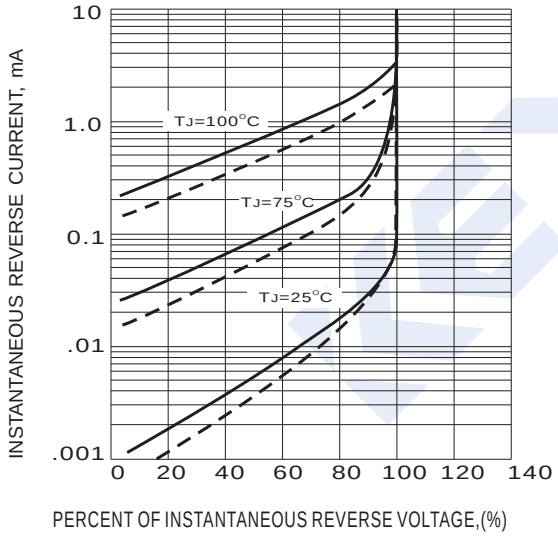

Fig.3- TYPICAL REVERSE CHARACTERISTIC

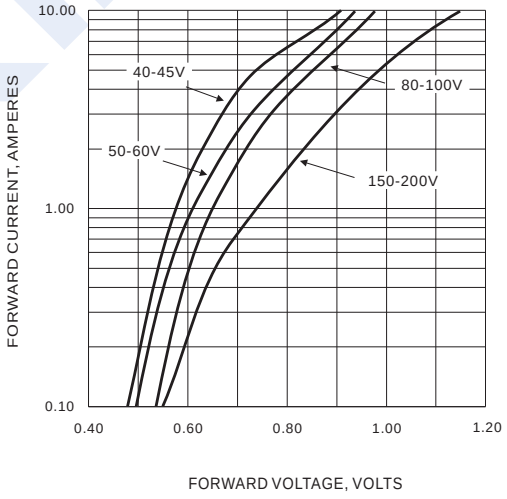

Fig.4- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC